

IN THE ABSTRACT

Delete the present abstract and, in its place, insert the following new abstract:

A cobalt silicide fabrication process entails first depositing a cobalt layer (120) on a silicon-containing EPROM region. A titanium layer (130) is formed over the cobalt layer by ionized physical vapor deposition ("IPVD") to protect the cobalt layer from contaminant gases. Cobalt of the cobalt layer is reacted with silicon of the EPROM region to form a cobalt silicide layer (210) after which the titanium layer and any unreacted cobalt are removed. Use of IPVD to form the titanium layer improves the step coverage to produce a better cobalt silicide layer.

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